

L Number	Hits	Search Text	DB	Time stamp
4	17	(flow adj rate) and 117/3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/02 09:47
6	94	(flow adj rate) same (hydrogen or inert or Ar or argon) and (IG or DZ or denuded or OSF or (stacking adj faults) or Oisf) and (anneal\$3 or rapid adj thermal or heat adj treat\$4 or rta ort rtp or ptp)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/02 10:28
8	79	(cooling adj rate) and (IG or DZ or denuded or OSF or (stacking adj faults) or Oisf) and (anneal\$3 or rapid adj thermal or heat adj treat\$4 or rta ort rtp or ptp) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/02 10:32
-	13	(anneal\$3 or (rapid adj thermal) or (heat adj treat\$4) or rta or rtp or ptp) and hydrogen and oxygen and wafer and 117/3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/28 15:41
-	81	(anneal\$3 or (rapid adj thermal) or (heat adj treat\$4) or rta or rtp or ptp) and (silicon same ingot) and (nitrogen or "n.sub.2") and (oxygen adj concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/28 15:54
-	33	(anneal\$3 or (rapid adj thermal) or (heat adj treat\$4) or rta or rtp or ptp) same (hydrogen or oxygen or nitrogen or inert) and wafer and 117/3.ccls. and temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/01 11:20
-	14	(anneal\$3 or (rapid adj thermal) or (heat adj treat\$4) or rta or rtp or ptp) and (((hydrogen or "h.sub.2") same (oxygen or "o.sub.2")))) and 117/3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/28 17:27
-	18	(((hydrogen or "h.sub.2") same (oxygen or "o.sub.2")))) and 117/3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/28 17:28
-	137	117/3.ccls. and ((nitrogen or "n.sub.2") or inert or argon or atmosphere or hydrogen or "h.sub.2") and temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/01 10:40
-	116	(anneal\$3 or (rapid adj thermal) or (heat adj treat\$4) or rta or rtp or ptp) and (IG or denuded or gettering) and temperature and wafer and silicon and (hydrogen or oxygen or inert or "h.sub.2" or "o.sub.2") and atmosphere and interstitial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/01 11:31
-	88	(anneal\$3 or (rapid adj thermal) or (heat adj treat\$4) or rta or rtp or ptp) same temperature and ingot and silicon and (nitrogen or "n.sub.2") and atmosphere and interstitial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/01 13:17
-	120	(anneal\$3 or (rapid adj thermal) or (heat adj treat\$4) or rta or rtp or ptp) same ingot same (nitrogen or "n.sub.2") same (hour or hr)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/01 13:54
-	154	((ramp adj rate) same temperature) and (RTP or anneal or (heat adj treat\$4)) and @py<2000	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/01 16:55

-	186	((rate) same temperature) and (RTP or anneal or (heat adj treat\$4)) and @py<2000 and (osf or osif or (stacking adj faults))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/01 17:20
-	93	((rate) same temperature) and (RTP or anneal or (heat adj treat\$4)) and @py<2000 and (osf or osif or (stacking adj faults)) and silicon adj (Wafer or substrate or ingot)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/01 17:25
-	51	((rate) same temperature) and (RTP or anneal or (heat adj treat\$4)) and @py<2000 and (IG or denuded) and silicon adj (Wafer or substrate or ingot)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/02 09:41